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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XFI

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, LVD, POR, PWM, WDT
Number of I/O	84
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D - 16bit; D/A - 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	121-LFBGA
Supplier Device Package	121-MAPBGA (8x8)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mkl36z256vmc4

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



- 16-bit low-power timer (LPTMR)
- Real time clock

Security and integrity modules

• 80-bit unique identification number per chip

Ordering Information ¹	
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Part Number	Me	Maximum number of I\O's	
	Flash (KB)	SRAM (KB)	
MKL36Z64VLH4	64	8	54
MKL36Z128VLH4	128	16	54
MKL36Z256VLH4	256	32	54
MKL36Z256VMP4	256	32	54
MKL36Z64VLL4	64	8	84
MKL36Z128VLL4	128	16	84
MKL36Z256VLL4	256	32	84
MKL36Z128VMC4	128	16	84
MKL36Z256VMC4	256	32	84

1. To confirm current availability of ordererable part numbers, go to http://www.freescale.com and perform a part number search.

Related Resources

Туре	Description	Resource
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	Solution Advisor
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KL36P121M48SF4RM ¹
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	KL36P121M48SF4 ¹
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	KINETIS_L_xN40H ²
Package	Package dimensions are provided in package drawings.	LQFP 64-pin: 98ASS23234W ¹
drawing		MAPBGA 64-pin: 98ASA00420D ¹
		LQFP 100-pin: 98ASS23308W ¹
		MAPBGA 121-pin: 98ASA00344D ¹

- 1. To find the associated resource, go to http://www.freescale.com and perform a search using this term.
- 2. To find the associated resource, go to http://www.freescale.com and perform a search using this term with the "x" replaced by the revision of the device you are using.



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{LVW1H}	Level 1 falling (LVWV = 00)	2.62	2.70	2.78	V	
V _{LVW2H}	 Level 2 falling (LVWV = 01) 	2.72	2.80	2.88	V	
V _{LVW3H}	 Level 3 falling (LVWV = 10) 	2.82	2.90	2.98	V	
V _{LVW4H}	Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range		±60		mV	
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	_
	Low-voltage warning thresholds — low range					1
V _{LVW1L}	• Level 1 falling (LVWV = 00)	1.74	1.80	1.86	v	
V _{LVW2L}	 Level 2 falling (LVWV = 01) 	1.84	1.90	1.96	v	
V _{LVW3L}	 Level 3 falling (LVWV = 10) 	1.94	2.00	2.06	v	
V _{LVW4L}	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	v	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	_	±40	_	mV	_
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	—
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	—

 Table 6.
 V_{DD} supply LVD and POR operating requirements (continued)

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors Table 7. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad (except RESET_b)	V ₂₂ = 0.5		V	1, 2
	 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -5 mA 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -2.5 mA 	V _{DD} – 0.5	—	v	
V _{OH}	Output high voltage — High drive pad (except RESET_b) • 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -20 mA • 1.71 V \leq V _{DD} \leq 2.7 V, I _{OH} = -10 mA	V _{DD} – 0.5 V _{DD} – 0.5		V V	1, 2
I _{ОНТ}	Output high current total for all ports	_	100	mA	
V _{OL}	Output low voltage — Normal drive pad • 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 5 mA • 1.71 V \leq V _{DD} \leq 2.7 V, I _{OL} = 2.5 mA		0.5 0.5	V V	1

Table continues on the next page...



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	• VLLS1 → RUN	_	112	124	μs	
	• VLLS3 \rightarrow RUN					
		—	53	60	μs	
	• LLS \rightarrow RUN					
		—	4.5	5.0	μs	
	 VLPS → RUN 					
		—	4.5	5.0	μs	
	• STOP \rightarrow RUN					
		—	4.5	5.0	μs	

 Table 8. Power mode transition operating behaviors (continued)

1. Normal boot (FTFA_FOPT[LPBOOT]=11).

2.2.5 Power consumption operating behaviors

The maximum values stated in the following table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Symbol	Description		Тур.	Max	Unit	Note
I _{DDA}	Analog supply current	—	—	See note	mA	1
IDD_RUNCO_ CM	Run mode current in compute operation - 48 MHz core / 24 MHz flash/ bus disabled, LPTMR running using 4 MHz internal reference clock, CoreMark® benchmark code executing from flash, at 3.0 V		6.7		mA	2
I _{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash, at 3.0 V		4.5	5.1	mA	3
I _{DD_RUN}	Run mode current - 48 MHz core / 24	at 1.8 V	5.6	6.3	mA	3
	- 48 MHz core / 24 MHz flash/ bus disabled, LPTMR running using 4 MHz internal reference clock, CoreMark® benchmark code executing from flash, at 3.0 V _RUNCO Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash, at 3.0 V D_RUN Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code executing from flash D_RUN Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code executing from flash, at 1.8 V Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code executing from flash, at 1.8 V Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code executing from flash, at 2.8 V	at 3.0 V	5.4	6.0	mA	
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code executing from flash, at 1.8 V	_	6.9	7.3	mA	3, 4
	Run mode current - 48 MHz core / 24	at 25 °C	6.9	7.1	mA	
	MHz bus and flash, all peripheral clocks enabled, code executing from flash, at 3.0 V	at 125 °C	7.3	7.6	mA	

 Table 9. Power consumption operating behaviors

Table continues on the next page ...

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Symbol	Description			٦	empera	ature (°0	C)		Unit
			-40	25	50	70	85	105	
I _{IREFSTEN4MHz}	4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.		56	56	56	56	56	56	μA
I _{IREFSTEN32KHz}	32 kHz internal reference clock Measured by entering STOP n 32 kHz IRC enabled.	(IRC) adder. node with the	52	52	52	52	52	52	μA
I _{EREFSTEN4MHz}	External 4 MHz crystal clock a Measured by entering STOP o with the crystal enabled.	dder. r VLPS mode	206	228	237	245	251	258	μA
I _{EREFSTEN32KHz}	External 32 kHz crystal clock	VLLS1	440	490	540	560	570	580	nA
	adder by means of the	VLLS3	440	490	540	560	570	580	
	EREFSTEN] bits. Measured	LLS	490	490	540	560	570	680	
	by entering all modes with the	VLPS	510	560	560	560	610	680	
	crystal enabled.	STOP	510	560	560	560	610	680	1
I _{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.		22	22	22	22	22	22	μA
I _{RTC}	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption		432	357	388	475	532	810	nA
I _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μΑ
	115200 baud rate. Includes selected clock source power consumption.	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I _{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output	MCGIRCLK (4 MHz internal reference clock)	86	86	86	86	86	86	μΑ
	compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.	OSCERCLK (4 MHz external crystal)	235	256	265	274	280	287	

Table 10. Low power mode peripheral adders — typical value

Table continues on the next page...





Figure 3. Run mode supply current vs. core frequency



3.1.1 SWD electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

Table 17. SWD full voltage range electricals



Figure 5. Serial wire clock input timing





Figure 6. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 18. MCG specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal V_{DD} and 25 °C	_	32.768	—	kHz	
f _{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	_	39.0625	kHz	
$\Delta_{fdco_res_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using C3[SCTRIM] and C4[SCFTRIM]	—	± 0.3	± 0.6	%f _{dco}	1

Table continues on the next page...



- 3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
- 4. When low power mode is selected, R_F is integrated and must not be attached externally.
- 5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications Table 20. Oscillator frequency specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{osc_lo}	Oscillator crystal or resonator frequency — low- frequency mode (MCG_C2[RANGE]=00)	32	_	40	kHz	
f _{osc_hi_1}	Oscillator crystal or resonator frequency — high- frequency mode (low range) (MCG_C2[RANGE]=01)	3		8	MHz	
f _{osc_hi_2}	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8		32	MHz	
f _{ec_extal}	Input clock frequency (external clock mode)	_	—	48	MHz	1, 2
t _{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t _{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	_	750	_	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	_	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	_	0.6	_	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	_	1	_	ms	

- 1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
- 2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
- 3. Proper PC board layout procedures must be followed to achieve specifications.
- 4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.



3.4.1.3 Flash high voltage current behaviors Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation		2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation		1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes				
Program Flash										
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	_	years	—				
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	—	years	—				
n _{nvmcycp}	Cycling endurance	10 K	50 K		cycles	2				

 Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

2. Cycling endurance represents number of program/erase cycles at -40 °C \leq T_j \leq 125 °C.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 25 and Table 26 are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.



3.6.1.1 16-bit ADC operating conditions Table 25. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	_
ΔV_{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	
V _{REFL}	ADC reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	
V _{ADIN}	Input voltage	16-bit differential mode	VREFL	—	31/32 * VREFH	V	—
		All other modes	VREFL	—	VREFH		
C _{ADIN}	Input	16-bit mode	_	8	10	pF	—
	capacitance	 8-bit / 10-bit / 12-bit modes 	—	4	5		
R _{ADIN}	Input series resistance		—	2	5	kΩ	_
R _{AS}	Analog source resistance (external)	13-bit / 12-bit modes f _{ADCK} < 4 MHz	_	_	5	kΩ	3
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0		18.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C _{rate}	ADC conversion rate	 ≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time 	20.000		818.330	Ksps	5
C _{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	_	461.467	Ksps	5

- 1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
- 2. DC potential difference.
- 3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
- 4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
- 5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.



Symbol	Description	Min.	Тур.	Max.	Unit
V _{DD}	Supply voltage	1.71	_	3.6	V
I _{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I _{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	_	_	20	μA
V _{AIN}	Analog input voltage	$V_{SS} - 0.3$	_	V _{DD}	V
V _{AIO}	Analog input offset voltage	_	_	20	mV
V _H	Analog comparator hysteresis ¹				
	 CR0[HYSTCTR] = 00 	—	5	—	mV
	• CR0[HYSTCTR] = 01	_	10	_	mV
	• CR0[HYSTCTR] = 10	_	20	_	mV
	 CR0[HYSTCTR] = 11 	—	30	_	mV
V _{CMPOh}	Output high	V _{DD} – 0.5		_	V
V _{CMPOI}	Output low	_	_	0.5	V
t _{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t _{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	_	_	40	μs
I _{DAC6b}	6-bit DAC current adder (enabled)	_	7	—	μA
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3		0.3	LSB

3.6.2 CMP and 6-bit DAC electrical specifications Table 27. Comparator and 6-bit DAC electrical specifications

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD} -0.6 V.

 Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.

3. 1 LSB = V_{reference}/64





Figure 12. Typical INL error vs. digital code



Num.	Symbol	Description	Min.	Max.	Unit	Note
8	t _v	Data valid (after SPSCK edge)	—	52	ns	—
9	t _{HO}	Data hold time (outputs)	0	—	ns	—
10	t _{RI}	Rise time input	-	t _{periph} - 25	ns	
	t _{FI}	Fall time input				
11	t _{RO}	Rise time output		36	ns	—
	t _{FO}	Fall time output				

 Table 31. SPI master mode timing on slew rate enabled pads (continued)

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).

2. $t_{periph} = 1/f_{periph}$



1. If configured as an output.

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA = 0)



Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{op}	Frequency of operation	0	f _{periph} /4	Hz	1
2	t _{SPSCK}	SPSCK period	4 x t _{periph}	_	ns	2
3	t _{Lead}	Enable lead time	1	_	t _{periph}	—
4	t _{Lag}	Enable lag time	1	_	t _{periph}	_
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	_	ns	_
6	t _{SU}	Data setup time (inputs)	2	_	ns	—
7	t _{HI}	Data hold time (inputs)	7	_	ns	_
8	t _a	Slave access time	—	t _{periph}	ns	3
9	t _{dis}	Slave MISO disable time	—	t _{periph}	ns	4
10	t _v	Data valid (after SPSCK edge)	_	122	ns	_
11	t _{HO}	Data hold time (outputs)	0	_	ns	—
12	t _{RI}	Rise time input	—	t _{periph} - 25	ns	—
	t _{FI}	Fall time input				
13	t _{RO}	Rise time output	—	36	ns	—
	t _{FO}	Fall time output				

Table 33. SPI slave mode timing on slew rate enabled pads

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).

2.

- $t_{periph} = 1/f_{periph}$ Time to data active from high-impedance state З.
- 4. Hold time to high-impedance state









Figure 17. SPI slave mode timing (CPHA = 1)

3.8.2 Inter-Integrated Circuit Interface (I2C) timing Table 34. I2C timing

Characteristic	Symbol	Standa	rd Mode	Fast	Unit	
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f _{SCL}	0	100	0	400 ¹	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t _{HD} ; STA	4	_	0.6	_	μs
LOW period of the SCL clock	t _{LOW}	4.7	—	1.3	_	μs
HIGH period of the SCL clock	t _{HIGH}	4	—	0.6	_	μs
Set-up time for a repeated START condition	t _{SU} ; STA	4.7	_	0.6	_	μs
Data hold time for I ² C bus devices	t _{HD} ; DAT	0 ²	3.45 ³	04	0.9 ²	μs
Data set-up time	t _{SU} ; DAT	250 ⁵	—	100 ³ , ⁶	_	ns
Rise time of SDA and SCL signals	t _r		1000	20 +0.1C _b ⁷	300	ns
Fall time of SDA and SCL signals	t _f	—	300	20 +0.1C _b ⁶	300	ns
Set-up time for STOP condition	t _{SU} ; STO	4	—	0.6	_	μs
Bus free time between STOP and START condition	t _{BUF}	4.7	—	1.3	—	μs
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	N/A	N/A	0	50	ns

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only achieved when using the High drive pins (see Voltage and current operating behaviors) or when using the Normal drive pins and VDD ≥ 2.7 V



Num.	Characteristic	Min.	Max.	Unit
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	_	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	-	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	87	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	-	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	72	ns

Table 38. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear



Figure 22. I2S/SAI timing — slave modes

3.9 Human-machine interfaces (HMI)

3.9.1 TSI electrical specifications

Table 39. TSI electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	μA

Table continues on the next page...

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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	• RVTRIM=0111	—	1.08	—		
	• RVTRIM=1111	—	1.09	-		
Δ _{RTRIM}	V _{IREG} TRIM resolution	_	—	3.0	% V _{IREG}	
I _{VIREG}	V _{IREG} current adder — RVEN = 1	_	1	—	μA	4
I _{RBIAS}	RBIAS current adder					
	 LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF) 	—	10	_	μA	
	 LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF) 	_	1	_	μA	
R _{RBIAS}	RBIAS resistor values					
	 LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF) 	—	0.28	_	MΩ	
	 LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF) 	—	2.98	_	MΩ	
VLL1	VLL1 voltage	—	_	V _{IREG}	V	5
VLL2	VLL2 voltage	_	_	2 x V _{IREG}	V	5
VLL3	VLL3 voltage	_	_	3 x V _{IREG}	V	5
VLL1	VLL1 voltage	—	_	V _{DDA} / 3	V	6
VLL2	VLL2 voltage	—	—	V _{DDA} / 1.5	V	6
VLL3	VLL3 voltage		—	V _{DDA}	V	6

Table 40. LCD electricals (continued)

- 1. The actual value used could vary with tolerance.
- 2. For highest glass capacitance values, LCD_GCR[LADJ] should be configured as specified in the LCD Controller chapter within the device's reference manual.
- 3. V_{IREG} maximum should never be externally driven to any level other than V_{DD} 0.15 V
- 4. 2000 pF load LCD, 32 Hz frame frequency
- VLL1, VLL2 and VLL3 are a function of V_{IREG} only when the regulator is enabled (GCR[RVEN]=1) and the charge pump is enabled (GCR[CPSEL]=1).
- 6. VLL1, VLL2 and VLL3 are a function of V_{DDA} only under either of the following conditions:
 - The charge pump is enabled (GCR[CPSEL]=1), the regulator is disabled (GCR[RVEN]=0), and VLL3 = V_{DDA} through the internal power switch (GCR[VSUPPLY]=0).
 - The resistor bias string is enabled (GCR[CPSEL]=0), the regulator is disabled (GCR[RVEN]=0), and VLL3 is connected to V_{DDA} externally (GCR[VSUPPLY]=1).

4 Dimensions

4.1 Obtaining package dimensions

Package dimensions are provided in package drawings.



To find a package drawing, go to **freescale.com** and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
64-pin LQFP	98ASS23234W
64-pin MAPBGA	98ASA00420D
100-pin LQFP	98ASS23308W
121-pin MAPBGA	98ASA00344D

5 Pinout

5.1 KL36 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

121 BGA	100 LQFP	64 BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
E4	1	A1	1	PTE0	DISABLED	LCD_P48	PTE0	SPI1_MISO	UART1_TX	RTC_ CLKOUT	CMP0_OUT	I2C1_SDA	LCD_P48
E3	2	B1	2	PTE1	DISABLED	LCD_P49	PTE1	SPI1_MOSI	UART1_RX		SPI1_MISO	I2C1_SCL	LCD_P49
E2	3	-	_	PTE2	DISABLED	LCD_P50	PTE2	SPI1_SCK					LCD_P50
F4	4	-	—	PTE3	DISABLED	LCD_P51	PTE3	SPI1_MISO			SPI1_MOSI		LCD_P51
H7	5		—	PTE4	DISABLED	LCD_P52	PTE4	SPI1_PCS0					LCD_P52
G4	6	Ι	—	PTE5	DISABLED	LCD_P53	PTE5						LCD_P53
F3	7	-	-	PTE6	DISABLED	LCD_P54	PTE6			I2S0_MCLK	audioUSB_ SOF_OUT		LCD_P54
E6	8	-	3	VDD	VDD	VDD							
G7	9	C4	4	VSS	VSS	VSS							
L6	_	I	—	VSS	VSS	VSS							
H1	14	E1	5	PTE16	ADC0_DP1/ ADC0_SE1	LCD_P55/ ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_ CLKIN0			LCD_P55
H2	15	D1	6	PTE17	ADC0_DM1/ ADC0_SE5a	LCD_P56/ ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_ CLKIN1		LPTMR0_ ALT3	LCD_P56
J1	16	E2	7	PTE18	ADC0_DP2/ ADC0_SE2	LCD_P57/ ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO		LCD_P57



7 Part identification

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values	
Q	Qualification status	 M = Fully qualified, general market flow P = Prequalification 	
KL##	Kinetis family	• KL36	
A	Key attribute	• Z = Cortex-M0+	
FFF	Program flash memory size	 64 = 64 KB 128 = 128 KB 256 = 256 KB 	
R	Silicon revision	 (Blank) = Main A = Revision after main 	
Т	Temperature range (°C)	• V = -40 to 105	
PP	Package identifier	 LH = 64 LQFP (10 mm x 10 mm) MP = 64 MAPBGA (5 mm x 5 mm) LL = 100 LQFP (14 mm x 14 mm) MC = 121 MAPBGA (8 mm x 8 mm) 	
СС	Maximum CPU frequency (MHz)	• 4 = 48 MHz	
N	Packaging type	• R = Tape and reel	

Table 41. Part number fields descriptions



8.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Тур.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μΑ

8.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



8.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):